



Patent  
Attorney's Docket No. 001425-104

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

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Masahiko TANAKA et al.

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Group Art Unit: 1763

Application No.: 09/862,458

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Examiner: Karla A. Moore

Filed: May 23, 2001

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Confirmation No.: 7476

For: THIN-FILM DISPOSITION  
APPARATUS

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#5A  
2/11/03  
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AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Official Action dated November 6, 2002, please amend the  
above-identified patent application as follows:

IN THE SPECIFICATION:

Please replace paragraphs 25 and 54 as follows:

A.  
[0025] In the above-mentioned thin-film deposition apparatus according to the present  
invention, the above-mentioned plurality of holes through which the radicals pass are  
preferably formed so as to satisfy the condition  $uL/D > 1$ , where  $u$  is the gas flow rate  
inside these holes,  $L$  is the effective length of the holes (in the embodiments shown in  
Figures 2, 3 and 4, this length is equivalent to the thickness of dividing plate 24), and  $D$  is  
the gas interdiffusion coefficient (the gas interdiffusion coefficient of the precursor gas and  
the gas introduced in the plasma discharge space at the holes). In a thin-film deposition

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